



Zener diode

Features

- 1. Small surface mounting type
- 2. High reliability



Applications

Voltage stabilization

Absolute Maximum Ratings

T_j=25 °C

Parameter	Test Conditions	Type	Symbol	Value	Unit
Power dissipation	$R_{thJA} \leq 300K/W$		P _V	500	mW
Z-current			I _Z	P _V /V _Z	mA
Junction temperature			T _j	175	°C
Storage temperature range			T _{stg}	-65~+175	°C

Stresses exceeding maximum ratings may damage the device. Maximum ratings are stress ratings only. Functional operation above the recommended operating conditions is not implied. Extended exposure to stresses above the recommended operating conditions may affect device reliability.

Electrical Characteristics

T_j=25 °C

Parameter	Test Conditions	Type	Symbol	Min	Typ	Max	Unit
Forward voltage	I _F =200mA		V _F			1.5	V



Type	V _{Znom}	I _{ZT}	for V _{ZT} and	r _{ZT}	r _{ZK} at	I _{ZK}	I _R and	I _R at	V _R	TK _{VZ}
LL55B	V	mA	V	Ω	Ω	mA	μA	μA ¹⁾	V	%/K
2V0	2.0	5	1.96~2.04	<100	<600	1	<150	<300	1	-0.09~-0.06
2V2	2.2	5	2.15~2.25	<100	<600	1	<150	<300	1	-0.09~-0.06
2V4	2.4	5	2.35~2.45	<85	<600	1	<50	<100	1	-0.09~-0.06
2V7	2.7	5	2.64~2.76	<85	<600	1	<10	<50	1	-0.09~-0.06
3V0	3.0	5	2.94~3.06	<85	<600	1	<4	<40	1	-0.08~-0.05
3V3	3.3	5	3.24~3.36	<85	<600	1	<2	<40	1	-0.08~-0.05
3V6	3.6	5	3.52~3.68	<85	<600	1	<2	<40	1	-0.08~-0.05
3V9	3.9	5	3.82~3.98	<85	<600	1	<2	<40	1	-0.08~-0.05
4V3	4.3	5	4.22~4.38	<75	<600	1	<1	<20	1	-0.06~-0.03
4V7	4.7	5	4.6~4.8	<60	<600	1	<0.5	<10	1	-0.05~+0.02
5V1	5.1	5	5.0~5.2	<35	<550	1	<0.1	<2	1	-0.02~+0.02
5V6	5.6	5	5.48~5.72	<25	<450	1	<0.1	<2	1	-0.05~+0.05
6V2	6.2	5	6.08~6.32	<10	<200	1	<0.1	<2	2	0.03~0.06
6V8	6.8	5	6.66~6.94	<8	<150	1	<0.1	<2	3	0.03~0.07
7V5	7.5	5	7.35~7.65	<7	<50	1	<0.1	<2	5	0.03~0.07
8V2	8.2	5	8.04~8.36	<7	<50	1	<0.1	<2	6.2	0.03~0.08
9V1	9.1	5	8.92~9.28	<10	<50	1	<0.1	<2	6.8	0.03~0.09
10	10	5	9.8~10.2	<15	<70	1	<0.1	<2	7.5	0.03~0.1
11	11	5	10.78~11.22	<20	<70	1	<0.1	<2	8.2	0.03~0.11
12	12	5	11.76~12.24	<20	<90	1	<0.1	<2	9.1	0.03~0.11
13	13	5	12.74~13.26	<26	<110	1	<0.1	<2	10	0.03~0.11
15	15	5	14.7~15.3	<30	<110	1	<0.1	<2	11	0.03~0.11
16	16	5	15.7~16.3	<40	<170	1	<0.1	<2	12	0.03~0.11
18	18	5	17.64~18.36	<50	<170	1	<0.1	<2	13	0.03~0.11
20	20	5	19.6~20.4	<55	<220	1	<0.1	<2	15	0.03~0.11
22	22	5	21.55~22.45	<55	<220	1	<0.1	<2	16	0.04~0.12
24	24	5	23.5~24.5	<80	<220	1	<0.1	<2	18	0.04~0.12
27	27	5	26.4~27.6	<80	<220	1	<0.1	<2	20	0.04~0.12
30	30	5	29.4~30.6	<80	<220	1	<0.1	<2	22	0.04~0.12
33	33	5	32.4~33.6	<80	<220	1	<0.1	<2	24	0.04~0.12
36	36	5	35.3~36.7	<80	<220	1	<0.1	<2	27	0.04~0.12
39	39	2.5	38.2~39.8	<90	<500	0.5	<0.1	<5	30	0.04~0.12
43	43	2.5	42.1~43.9	<90	<600	0.5	<0.1	<5	33	0.04~0.12
47	47	2.5	46.1~47.9	<110	<700	0.5	<0.1	<5	36	0.04~0.12
51	51	2.5	50~52	<125	<700	0.5	<0.1	<10	39	0.04~0.12
56	56	2.5	54.9~57.1	<135	<1000	0.5	<0.1	<10	43	0.04~0.12
62	62	2.5	60.8~63.2	<150	<1000	0.5	<0.1	<10	47	0.04~0.12
68	68	2.5	66.6~69.4	<200	<1000	0.5	<0.1	<10	51	0.04~0.12
75	75	2.5	73.5~76.5	<250	<1500	0.5	<0.1	<10	56	0.04~0.12

¹⁾ at T_j=150°C



Characteristics ($T_j=25$

$^{\circ}\text{C}$ unless otherwise specified)

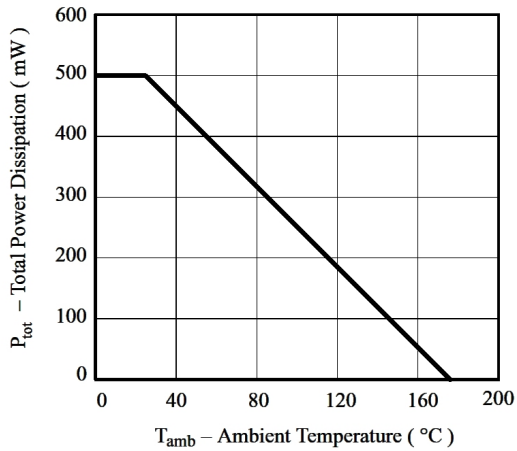


Figure 1. Total Power Dissipation vs. Ambient Temperature

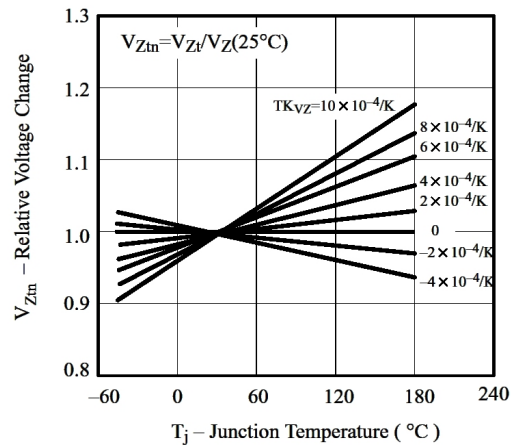


Figure 4. Typical Change of Working Voltage Vs. Junction Temperature

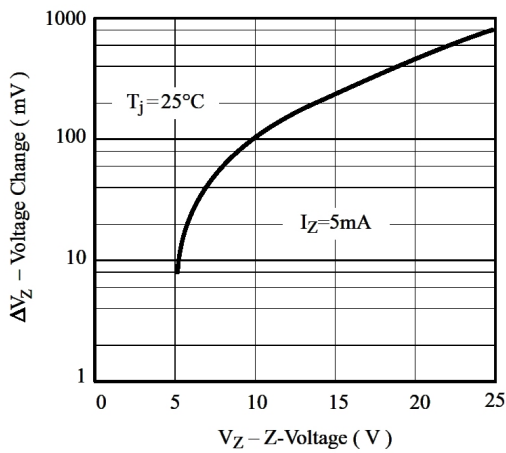


Figure 2. Typical Change of Working Voltage under Operating Conditions at $T_{amb}=25^{\circ}\text{C}$

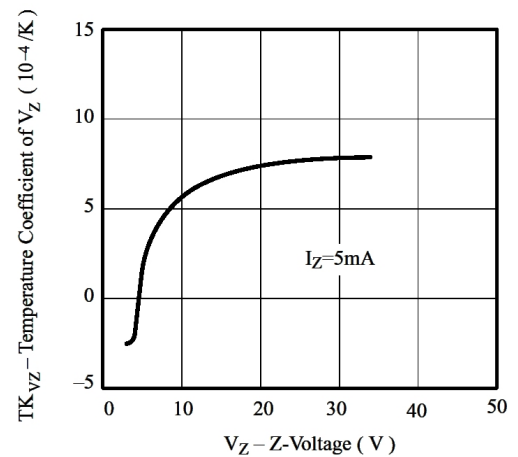


Figure 5. Temperature Coefficient of V_Z vs. Z-Voltage

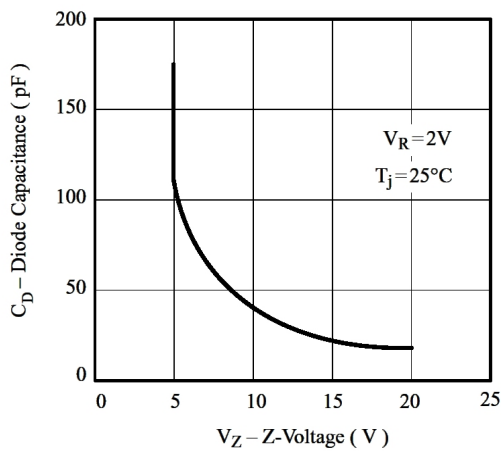


Figure 3. Diode Capacitance vs. Z-voltage

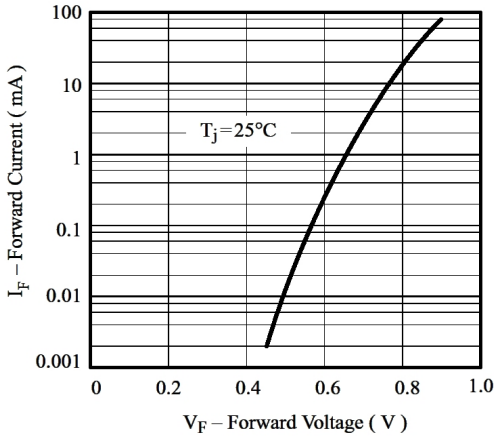


Figure 6. Forward Current vs. Forward Voltage

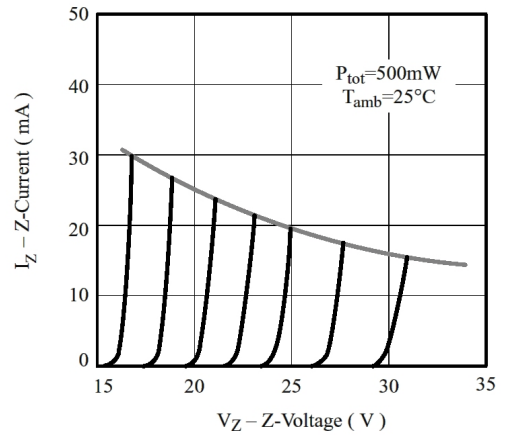


Figure 8. Z-Current vs. Z-Voltage

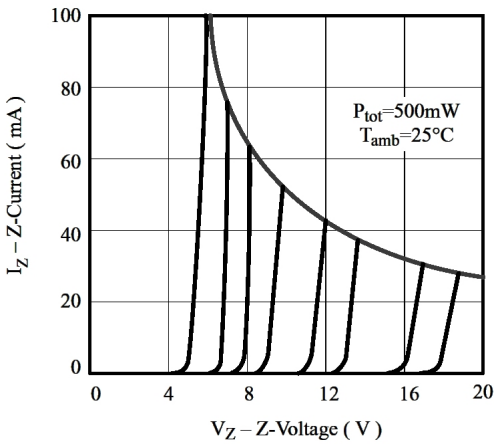


Figure 7. Z-Current vs. Z-Voltage

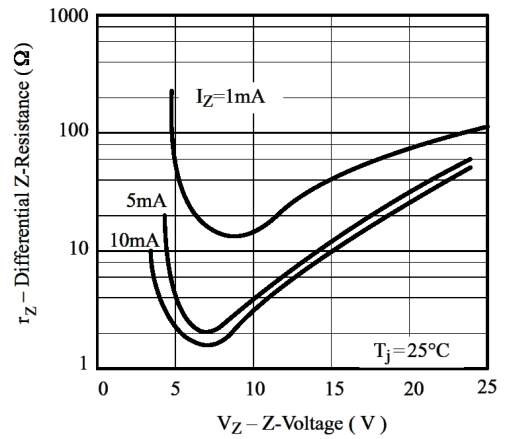
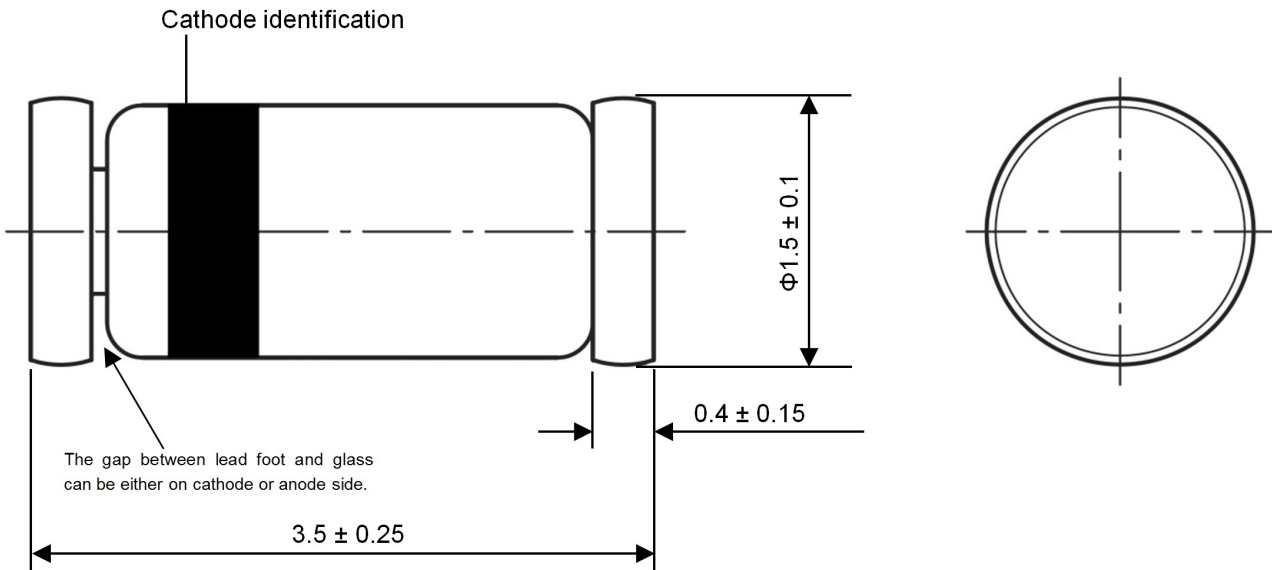


Figure 9. Differential Z-Resistance Vz vs. Z-Voltage



Dimensions in mm



Glass Case
Mini Melf / SOD-80
JEDEC DO-213 AA